PROCESS CP635

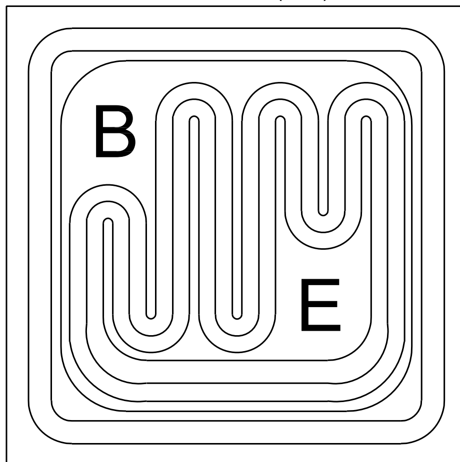
Power Transistor

PNP - Silicon Power Transistor Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	106 x 106 MILS
Die Thickness	12 MILS
Base Bonding Pad Area	25 x 33 MILS
Emitter Bonding Pad Area	30 x 36 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Ag - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER
920

PRINCIPAL DEVICE TYPE
MJ2955

R1 (29-April 2010)